

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

MAKITA et al.

Serial No. 09/667,527

Filed: September 22, 2000

For: METHOD OF PRODUCING SEMICONDUCTOR DEVICE



Atty. Ref.: 925-160

Group: 2812

Examiner:

\* \* \* \* \*

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INFORMATION DISCLOSURE STATEMENT**

- ☒ 1. **PTO-1449 Pursuant to 37 CFR 1.97(b)**  
[within 3 months of filing or prior to 1st Office Action] *N/C*
- ☐ 2. **Statement Pursuant to 37 CFR 1.97(c)**  
[before Final Office Action or Allowance] *N/C*
- ☐ 3. **Fee Payment Pursuant to 37 CFR 1.97(c)**  
[before Final Office Action or Allowance] *\$180.00*
- ☐ 4. **Pursuant to 37 CFR 1.97(d)**  
[before Issue Fee payment] *\$180.00*

The following are submitted in the above-identified application in compliance with 37 C.F.R. §§ 1.97 and 1.98:

- ☒ 5. A list of documents on Form PTO-1449 together with copies of each identified document and a translation or a concise explanation of each non-English language document is enclosed herewith.
- ☒ a) These references cited in a Taiwanese Office Action mailed June 9, 2003.

This paper is submitted in accordance with:


- ☒ 6. 37 CFR 1.97(b): [within 3 months of filing or prior to 1st Office Action]
- ☐ 7. 37 CFR 1.97(c): [before Final Office Action or Allowance, whichever is earlier]; and

- ☐ a) The required Statement made in item 9 below; or
- ☐ b) The \$180.00 fee specified in 37 CFR §1.17(p) for submission of this Information Disclosure Statement is authorized in item 10 below.
- ☐ 8. 37 CFR §1.97(d): [before issue fee payment]; and
- ☐ a) The fee (\$180.00) required by 37 CFR §1.17(p) is submitted herewith; and
- ☐ b) The required Statement is stated in item 9 below.
- ☐ 9. Statement under 37 CFR 1.97(e)
- ☐ a) The undersigned attorney of record hereby certifies under 37 C.F.R. §1.97(e) that each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement (each item contained in this IDS was the first citation of that item by a foreign patent office in a counterpart foreign application which occurred no more than three months prior to the filing of this IDS); or
- ☐ b) No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this Statement, after making reasonable inquiry, no item of information contained in this Statement was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement.
- ☒ 10. Please charge all deficiency fees associated with the submission of this Information Disclosure Statement and any other fees applicable to this application to Deposit Account No. 14-1140. An original and one (1) copy of this document are enclosed.

Respectfully submitted,  
NIXON & VANDERHYE P.C.

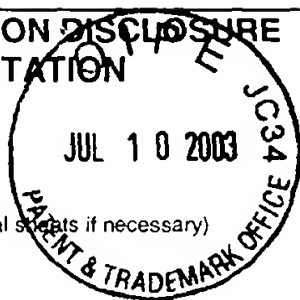
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INFORMATION DISCLOSURE  
CITATION

(Use several sheets if necessary)



ATTY. DOCKET NO.

925-160

APPLICANT

MAKITA et al.

FILING DATE

September 22, 2000

SERIAL NO.

09/667,527

GROUP

2812

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO

## OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	Lee et al, "Fabrication of High-Mobility p-Channel Poly-Si Thin Film Transistors by Self-Aligned Metal-Induced Lateral Crystallization", IEEE Electron Device Letters, vol. 17, no. 8, August 1996, pp. 407-409
	Bhat et al, "The Effects of MIC/MILC Interface on the Performance of MILC-TFTs", Device Research Conf., 1998, pp. 110-111
	Jin et al, "Performance of Thin-Film Transistors with Ultrathin Ni-MILC Polycrystalline Silicon Channel Layers", IEEE Electron Device Letters, vol. 20, no. 4, April 1999, pp. 167-169

*Examiner	Date Considered
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)